

Title (en)

Method for forming a trench isolation structure in an integrated circuit

Title (de)

Verfahren zur Herstellung einer Grabenstruktur für die Isolation in einer integrierten Schaltung

Title (fr)

Procédé pour former une structure de rainure pour isolation pour circuit intégré

Publication

EP 0736897 A3 19980311 (EN)

Application

EP 96104675 A 19960325

Priority

US 41624395 A 19950404

Abstract (en)

[origin: EP0736897A2] The reliability of integrated circuits fabricated with trench isolation is improved by forming a trench isolation structure with a void-free trench plug (36). In one embodiment, a polysilicon layer (28) is formed within a trench (22) and then subsequently oxidized to form a first dielectric layer (30). The first dielectric layer (30) is then etched and a second dielectric layer (34) is subsequently formed over the etched dielectric layer (32). A portion of the second dielectric layer (34) is then removed using chemical-mechanical polishing to form a void-free trench plug (36) within the trench (22). In addition, reliability is also improved by minimizing subsequent etching of trench plug (36) after it has been formed.

<IMAGE>

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CPC (source: EP KR US)

H01L 21/76224 (2013.01 - EP US); **H01L 27/04** (2013.01 - KR)

Citation (search report)

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